

ABSTRACT OF THE DISCLOSURE

An electron beam exposure apparatus which exposes a wafer (118) by using a plurality of electron beams corrects the positional error of the electron beams by using multi-deflector arrays (105, 106) capable of independently deflecting the positions of the electron beams, and pattern data to be projected onto the wafer (118). More specifically, when each of the electron beams is deflected to a predetermined exposure position on the basis of the pattern data, a static positional error independent of the deflection position is corrected by the multi-deflector arrays (105, 106), and a dynamic positional error depending on the deflection position is corrected on the basis of the pattern data.